



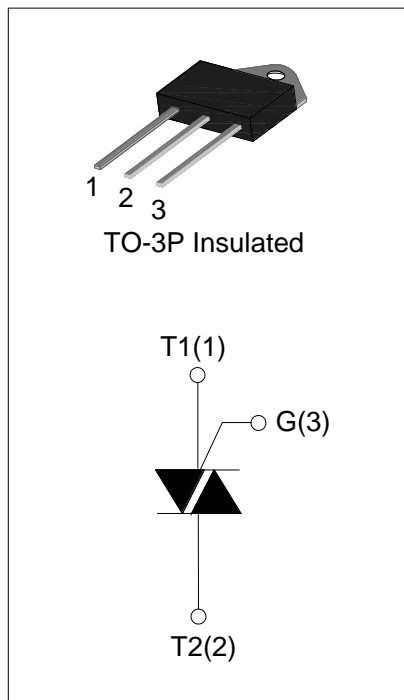
DESCRIPTION:

JST26Z provide high dv/dt rate with strong resistance to electromagnetic interference. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

JST26Z provide insulation voltage rated at 2500V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	600 and 800 and 1200	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	600/800/1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	600/800/1200	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-3P(Ins) ($T_C=100^\circ\text{C}$)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	250	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	340	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current		I_{GM}	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W

Peak gate power	P_{GM}	10	W
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ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

 V_{DRM}/V_{RRM} : 600/800V

Symbol	Test Condition	Quadrant		JST26Z-600/800V		Unit
				BW	CW	
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX	50	35	mA
V_{GT}		I - II -III	MAX	1.3		V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	80	70	mA
		II		100	80	
I_H	$I_T=100\text{mA}$		MAX	75	50	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	1000	500	V/ μs

 V_{DRM}/V_{RRM} : 1200V

Symbol	Test Condition	Quadrant		JST26Z-1200V		Unit
				BW	CW	
I_{GT}	$V_D=12V R_L=33\Omega$	I - II -III	MAX	50	35	mA
V_{GT}		I - II -III	MAX	1.5		V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	90	70	mA
		II		100	80	
I_H	$I_T=100\text{mA}$		MAX	80	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	1500	1000	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=35A t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	3	mA

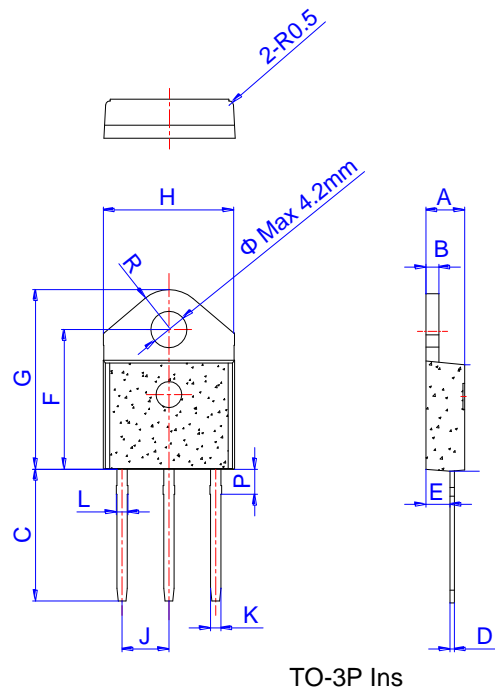
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-3P(Ins)	0.8	$^{\circ}C/W$

ORDERING INFORMATION

<p>J</p> <p>JieJie Microelectronics Co.,Ltd</p>	<p>ST</p> <p>Triacs</p> <p>$I_{T(RMS)}:25A$</p>	<p>26</p>	<p>Z</p> <p>Z:TO-3P(Ins)</p>	<p>-600</p> <p>600:$V_{DRM}/V_{RRM} \geq 600V$ 800:$V_{DRM}/V_{RRM} \geq 800V$ 1200:$V_{DRM}/V_{RRM} \geq 1200V$</p>	<p>BW</p> <p>BW:$I_{GT3} \leq 50mA$ CW:$I_{GT3} \leq 35mA$</p>
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PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

FIG.1: Maximum power dissipation versus RMS on-state current

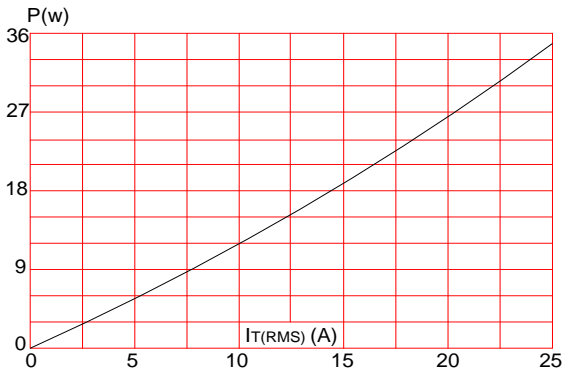


FIG.2: RMS on-state current versus case temperature

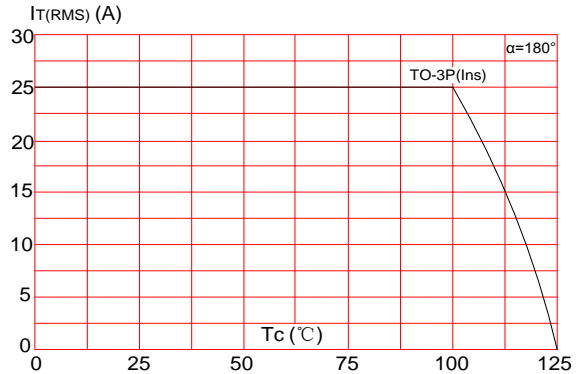


FIG.3: Surge peak on-state current versus number of cycles

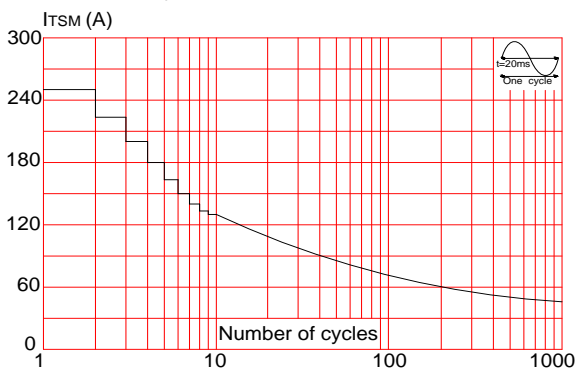


FIG.4: On-state characteristics (maximum values)

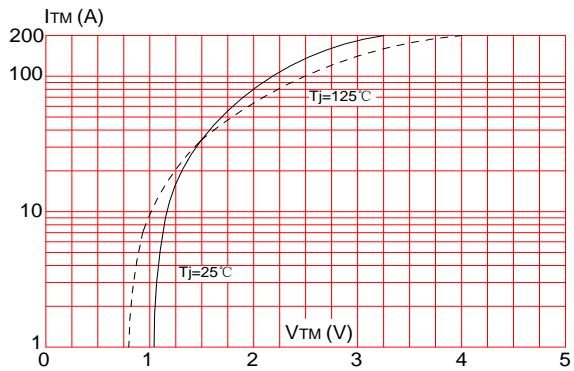


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

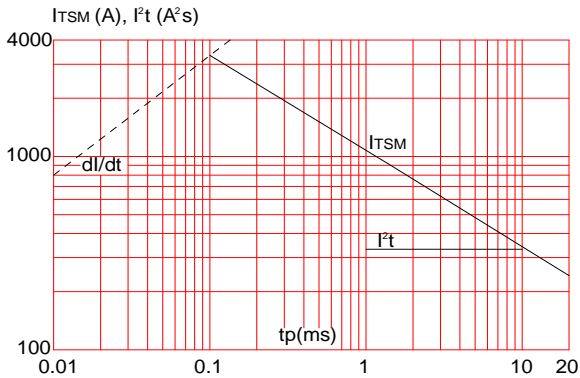
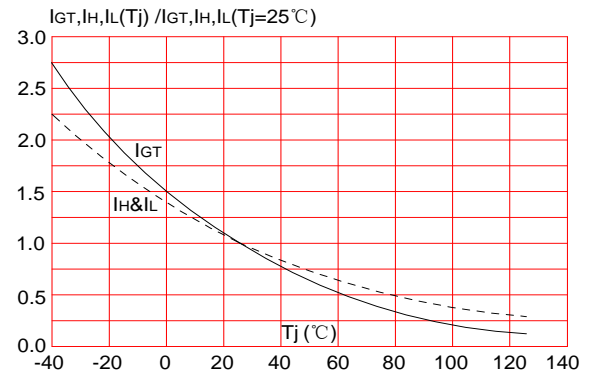



FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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